

ANTI-REFLECTIVE INTERPOLY DIELECTRIC

ABSTRACT

The invention provides core stacks for flash memory with an anti-reflective interpoly dielectric. Instead of requiring an anti-reflective coating at the top of the a stack, the present invention uses the interpoly layer as an anti-reflective coating in conjunction with a transmissive second polymer layer. Light is transmitted through the transmissive second polymer layer to the anti-reflective interpoly dielectric layer. The transmissive second polymer layer is formed from an amorphous silicon or polysilicon. Silicon oxynitride (SiON), as formed in the present invention, having a good dielectric constant K, is tailored in its index of refraction and in its thickness for utilization as both a good interpoly material and an anti-reflective coating.